



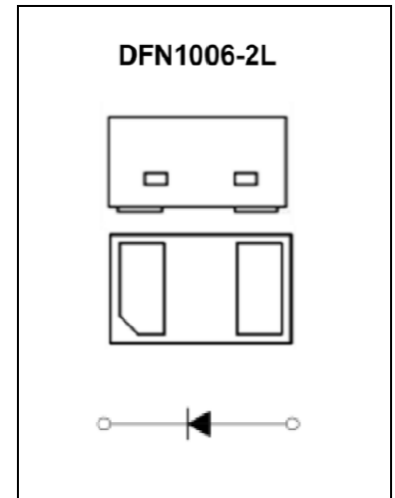
B1040A1 Schottky Barrier Diode

Feature

- Low Forward Voltage Drop
- Very Small SMD Package

Application

- Low Voltage Rectification
- High Efficiency DC/DC Conversion
- Switch Mode Power Supply
- Inverse Polarity Protection
- Low Power Consumption Applications



MARKING:



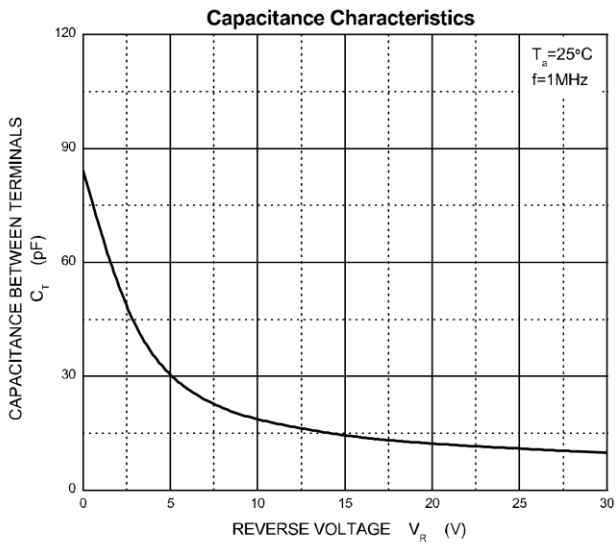
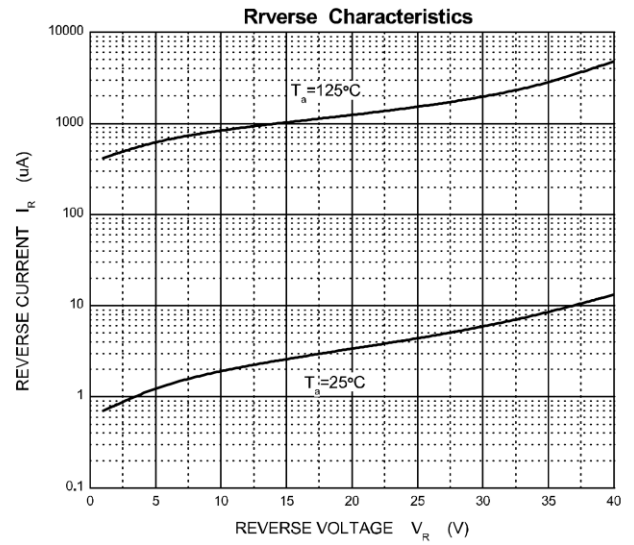
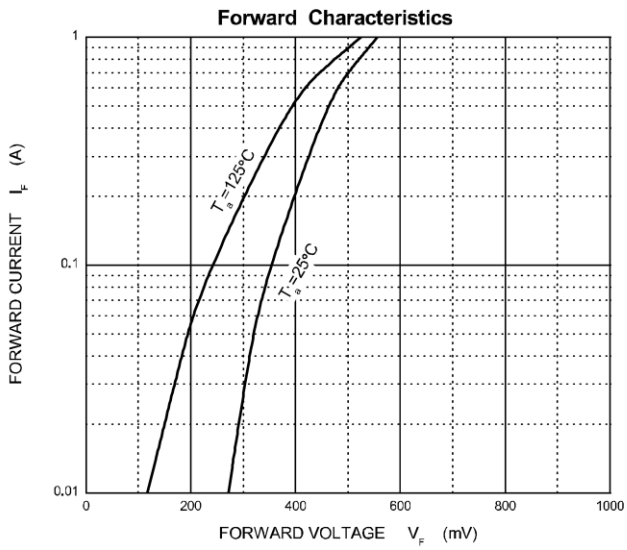
ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	1	A
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	7	A
Power Dissipation	P_D	0.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	400	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

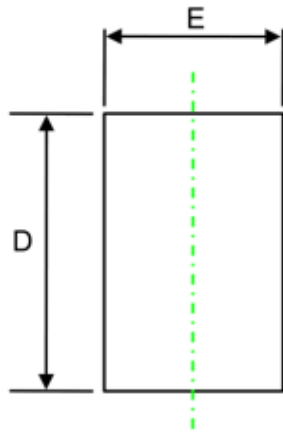
ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V_{BR}	$I_R = 1\text{mA}$	40			V
Reverse current	I_R	$V_R = 40\text{V}$		10	40	μA
Forward voltage	V_F	$I_F = 0.1\text{A}$		0.35	0.38	V
		$I_F = 0.2\text{A}$		0.37	0.42	V
		$I_F = 0.5\text{A}$		0.42	0.49	V
		$I_F = 0.7\text{A}$		0.47	0.55	V
		$I_F = 1\text{A}$		0.51	0.61	V
Total capacitance	C_{tot}	$V_R = 10\text{V}, f = 1\text{MHz}$		19		pF

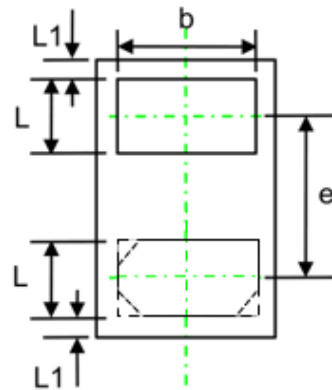
Typical Characteristics



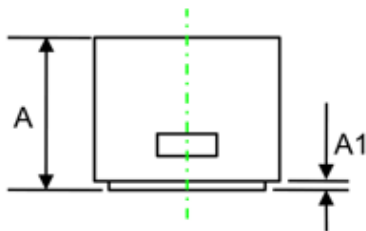
DFN1006-2L Package Outline Dimensions



TOP VIEW
[顶视图]



BOTTOM VIEW
[底视图]



SIDE VIEW
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.550	0.016	0.022
A1	0.000	0.050	0.000	0.002
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
b	0.400	0.600	0.016	0.024
e	0.65 TYP		0.026 TYP	
L1	0.05 REF		0.002 REF	
L	0.200	0.300	0.008	0.012